

# OPTICALLY PUMPED, SURFACE-EMITTING SEMICONDUCTOR LASER DEVICE AND A METHOD FOR PRODUCING THE SAME

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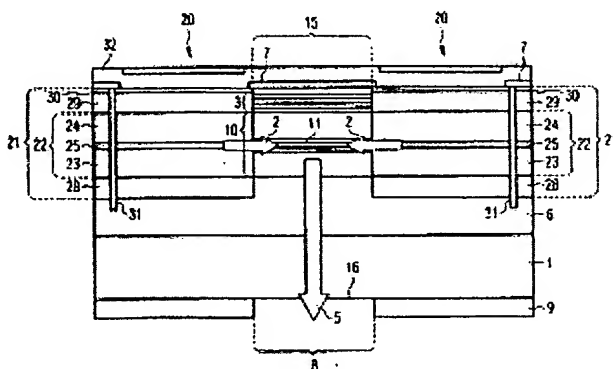
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## Abstract of DE10026734

The invention relates to an optically pumped, surface-emitting semiconductor laser device comprising at least one quantum well structure (11) which generates radiation and at least one pump radiation source (20) for optically pumping the quantum well structure (11), said pump radiation source (20) having a laterally-emitting semiconductor structure (21). The radiation generating quantum well structure (11) and the laterally-emitting semiconductor structure (21) are grown by epitaxy on a common substrate (1). This monolithically produced semiconductor laser device advantageously permits an extremely effective, homogeneous optical pumping of the radiation generating quantum well



- structure. The invention also relates to methods for producing inventive semiconductor laser devices.

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